DESCRIPTION

~~SOLAR CELL AND METHOD FOR MANUFACTURING SAME~~

TECHNICAL FIELD

[0001]

The present invention relates to a solar cell and a method for producing thereof.

BACKGROUND ART

[0002]

A previous back surface electrode-type solar cell is schematically shown in FIG. 14 as a cross sectional view. The back surface electrode-type solar cell 210 produced by a previous art will be described by referring to FIG. 14. On the light-receiving surface side of an N-type silicon substrate 213, a rugged shape 214 and an FSF (Front Surface Field) layer 215, which is an N-type diffusion layer, are formed. On the rugged shape 214, a dielectric passivation layer (a surface passivation layer) 217 which contains silicon dioxide and an antireflective film 216 which contains silicon nitride are formed from the side of the N-type diffusion layer 213.

[0003]

On the backside of the N-type silicon substrate 213, N-type doped N-type diffusion layers 220 and P-type doped P-type diffusion layers 221 are alternately formed. In addition, on the backside of the N-type silicon substrate 213, an oxide layer (the first backside passivation film) 219 is formed. On the N-type diffusion layer 220, an N-type contact electrode 211 is formed; and on the P-type diffusion layer 221, a P-type contact electrode 212 is formed. These contact electrodes, which are joined

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